



- 1 -

Socket No. 0756-2077

THE UNITED STATES PATENT AND TRADEMARK OFFICE

RECEIVED

NOV -7 2002

TC-2800 MAIL ROOM

In re Patent Application of

Shunpei YAMAZAKI et al.

Serial No. 09/466,828

Filed: December 20, 1999

For: INSULATING FILM AND

METHOD OF PRODUCING

SEMICONDUCTOR DEVICE

)

)

)

)

)

)

)

Art Unit: 2818

Examiner: R. Berry

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on 11/12/02

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

Please preliminarily amend the above-identified application as follows:

IN THE CLAIMS:

Please add new claim 30 as follows:

C¹
--30. A method of manufacturing a semiconductor device comprising:
forming a gate insulating film comprising silicon oxide on
a channel region by plasma CVD using a reactive gas comprising at least an
organic silane,

wherein said gate insulating film contains halogen at a
concentration of $5 \times 10^{20} \text{cm}^{-3}$ or less and carbon at a concentration of 5×10^{19}
 cm^{-3} or less. --

5/Pre-
Amend
C
G. Stucky
11-12-02